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Kind regards,

Team Nexperia



# **2PD601ART** 50 V, 100 mA NPN general-purpose transistor Rev. 01 — 15 March 2007

Product data sheet

#### **Product profile** 1.

#### 1.1 General description

NPN general-purpose transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

PNP complement: 2PB709ART.

#### 1.2 Features

- General-purpose transistor
- Small SMD plastic package

#### 1.3 Applications

General-purpose switching and amplification

#### 1.4 Quick reference data

#### Quick reference data Table 1. Symbol Parameter Conditions Min Тур Max Unit V<sub>CEO</sub> collector-emitter voltage open base --50 V $I_{C}$ collector current 100 mΑ - $h_{\text{FE}}$ DC current gain $V_{CE} = 10 V;$ 210 -340 $I_C = 2 \text{ mA}$

#### **Pinning information** 2.

Pin	Description	Simplified outline	Symbol
1	base		
2	emitter		3
3	collector		1



#### 50 V, 100 mA NPN general-purpose transistor

#### 3. Ordering information

Table 3. Order	3. Ordering information				
Type number	Package				
	Name	Description	Version		
2PD601ART	-	plastic surface-mounted package; 3 leads	SOT23		

#### 4. Marking

#### Table 4.Marking codes

Type number	Marking code <sup>[1]</sup>
2PD601ART	C3*

- [1] \* = -: made in Hong Kong
  - \* = p: made in Hong Kong
  - \* = t: made in Malaysia
  - \* = W: made in China

#### 5. Limiting values

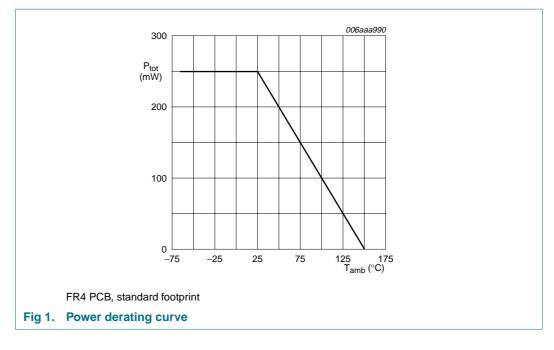
#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

		•••	,		
Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter	-	60	V
V <sub>CEO</sub>	collector-emitter voltage	open base	-	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	-	6	V
I <sub>C</sub>	collector current		-	100	mA
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms	-	200	mA
I <sub>BM</sub>	peak base current	single pulse; t <sub>p</sub> ≤ 1 ms	-	100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> -	250	mW
Tj	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		-65	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

#### 50 V, 100 mA NPN general-purpose transistor



### 6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	-	500	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		-	-	140	K/W

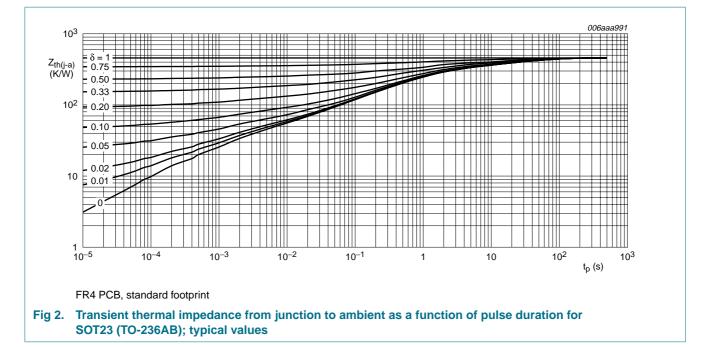
[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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### **2PD601ART**

#### 50 V, 100 mA NPN general-purpose transistor



#### 7. Characteristics

#### Table 7. Characteristics

 $T_{amb} = 25 \circ C$  unless otherwise specified.

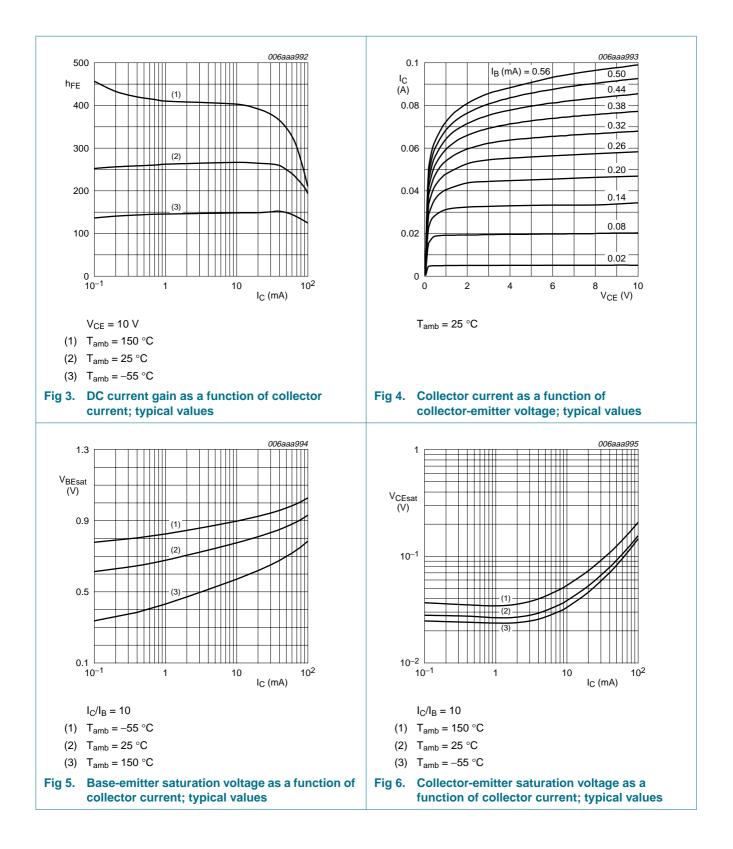
1 amb - 20	*C unless otherwise spec	cined:				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A}$	-	-	10	nA
	current	$V_{CB} = 60 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 ^{\circ}\text{C}$	-	-	5	μΑ
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 V; I_C = 0 A$	-	-	10	nA
h <sub>FE</sub>	DC current gain	V <sub>CE</sub> = 2 V; I <sub>C</sub> = 100 mA	90	-	-	
		$V_{CE} = 10 \text{ V};$ $I_C = 2 \text{ mA}$	210	-	340	
V <sub>CEsat</sub>	collector-emitter saturation voltage	I <sub>C</sub> = 100 mA; I <sub>B</sub> = 10 mA	<u>[1]</u> _	-	250	mV
f <sub>T</sub>	transition frequency	$V_{CE} = 10 V;$ $I_{C} = 2 mA;$ f = 100 MHz	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$\label{eq:VCB} \begin{split} V_{CB} &= 10 \text{ V};\\ I_E &= i_e = 0 \text{ A};\\ f &= 1 \text{ MHz} \end{split}$	-	-	3	pF

[1] Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

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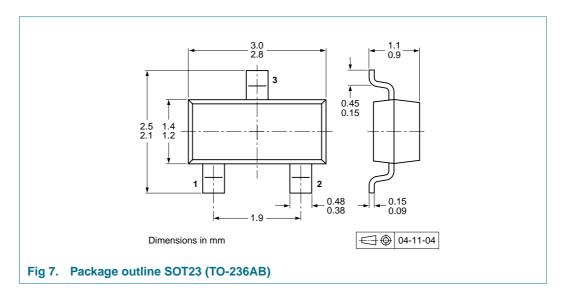
#### 50 V, 100 mA NPN general-purpose transistor



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50 V, 100 mA NPN general-purpose transistor

#### 8. Package outline



### 9. Packing information

#### Table 8. Packing methods

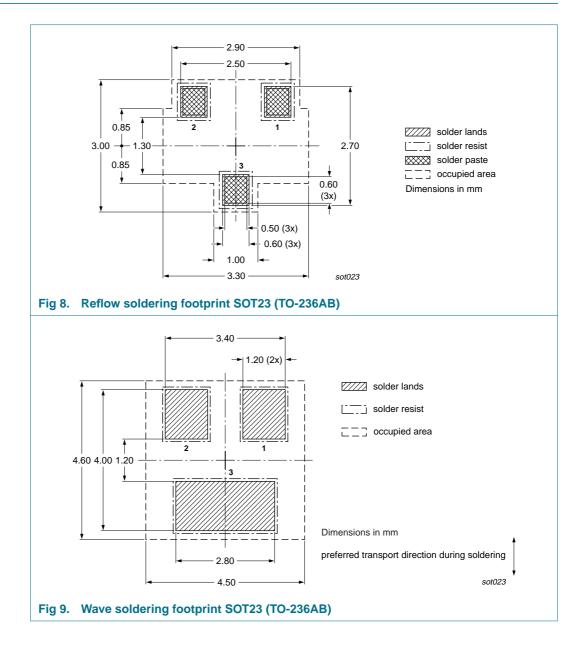
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
2PD601ART	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

[1] For further information and the availability of packing methods, see Section 13.

50 V, 100 mA NPN general-purpose transistor

### **10. Soldering**



#### 50 V, 100 mA NPN general-purpose transistor

### **11. Revision history**

Table 9. Revisi	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
2PD601ART_1	20070315	Product data sheet	-	-	

#### 50 V, 100 mA NPN general-purpose transistor

### **12. Legal information**

#### **12.1 Data sheet status**

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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### **2PD601ART**

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